

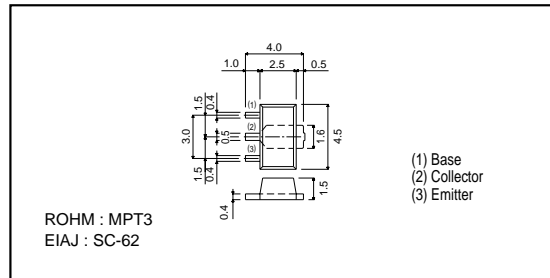
# Power transistor (−20V, −2A)

## 2SB1427

### ●Features

- 1) Low saturation voltage,  
typically  $V_{CE(sat)} = -0.5V$  at  $I_C/I_B = -1A / -50mA$ .
- 2) Excellent DC current gain characteristics.

### ●External dimensions (Units : mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CB0}$	-20	V
Collector-emitter voltage	$V_{CE0}$	-20	V
Emitter-base voltage	$V_{EB0}$	-6	V
Collector current	$I_C$	-2	A(DC)
		-3	A(Pulse) *1
Collector power dissipation	$P_C$	0.5	W
		2	W *2
Junction temperature	$T_J$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C

\*1 Single pulse,  $P_w=10ms$

\*2 When mounted on a 40×40×0.7mm ceramic board.

### ●Packaging specifications and hFE

Type	2SB1427
Package	MPT3
hFE	E
Marking	BJ *
Code	T100
Basic ordering unit (pieces)	1000

\* Denotes hFE

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CB0}$	-20	-	-	V	$I_C = -50\mu A$
Collector-emitter breakdown voltage	$BV_{CE0}$	-20	-	-	V	$I_C = -1mA$
Emitter-base breakdown voltage	$BV_{EB0}$	-6	-	-	V	$I_E = -50\mu A$
Collector cutoff current	$I_{CBO}$	-	-	-0.5	$\mu A$	$V_{CB} = -16V$
Emitter cutoff current	$I_{EBO}$	-	-	-0.5	$\mu A$	$V_{EB} = -5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.5	V	$I_C/I_B = -1A/-500mA$ *
DC current transfer ratio	hFE	390	-	820	-	$V_{CE}/I_C = -6V/-0.5A$
Transition frequency	f <sub>t</sub>	-	90	-	MHz	$V_{CE} = -10V, I_E = 10mA, f = 30MHz$
Output capacitance	C <sub>ob</sub>	-	30	-	pF	$V_{CB} = -10V, I_E = 0A, f = 1MHz$

\* Measured using pulse current.